

TIP33A, TIP33C

NPN High-Power Transistors

Designed for general-purpose power amplifier and switching applications.

Features

- ESD Ratings: Machine Model, C; > 400 V
Human Body Model, 3B; > 8000 V
- Epoxy Meets UL 94 V-0 @ 0.125 in
- Pb-Free Packages are Available*

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector – Emitter Voltage	TIP33A TIP33C V_{CEO}	60 100	Vdc
Collector – Base Voltage	TIP33A TIP33C V_{CBO}	60 100	Vdc
Emitter – Base Voltage	V_{EBO}	5.0	Vdc
Collector Current – Continuous – Peak (Note 1)	I_C	10 15	Adc Apk
Base Current – Continuous	I_B	3.0	Adc
Total Device Dissipation @ $T_C = 25^\circ\text{C}$ Derate above 25°C	P_D	80 0.64	Watts W/ $^\circ\text{C}$
Operating and Storage Junction Temperature Range	T_J, T_{stg}	-65 to +150	$^\circ\text{C}$

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	1.56	$^\circ\text{C/W}$
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	35.7	$^\circ\text{C/W}$

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

1. Pulse Test: Pulse Width $\leq 300 \mu\text{s}$, Duty Cycle $\leq 2.0\%$.

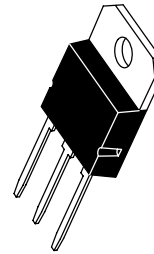
*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.



ON Semiconductor®

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**10 AMPERE
NPN SILICON
POWER TRANSISTORS
60 & 100 VOLT, 80 WATTS**



SOT-93 (TO-218)
CASE 340D
STYLE 1

MARKING DIAGRAM



A = Assembly Location
Y = Year
WW = Work Week
TIP33x = Device Code
x = A or C
G = Pb-Free Package

ORDERING INFORMATION

Device	Package	Shipping
TIP33A	TO-218	30 Units / Rail
TIP33AG	TO-218 (Pb-Free)	30 Units / Rail
TIP33C	TO-218	30 Units / Rail
TIP33CG	TO-218 (Pb-Free)	30 Units / Rail

TIP33A, TIP33C

ELECTRICAL CHARACTERISTICS ($T_C = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit	
OFF CHARACTERISTICS					
Collector–Emitter Sustaining Voltage (Note 2) ($I_C = 30\text{ mA}$, $I_B = 0$)	TIP33A TIP33C	$V_{CEO(sus)}$	60 100	– –	Vdc
Collector–Emitter Cutoff Current ($V_{CE} = 30\text{ V}$, $I_B = 0$) ($V_{CE} = 60\text{ V}$, $I_B = 0$)	TIP33A TIP33C	I_{CEO}	–	0.7	mA
Collector–Emitter Cutoff Current ($V_{CE} = \text{Rated } V_{CEO}$, $V_{EB} = 0$)		I_{CES}	–	0.4	mA
Emitter–Base Cutoff Current ($V_{EB} = 5.0\text{ V}$, $I_C = 0$)		I_{EBO}	–	1.0	mA
ON CHARACTERISTICS (Note 2)					
DC Current Gain ($I_C = 1.0\text{ A}$, $V_{CE} = 4.0\text{ V}$) ($I_C = 3.0\text{ A}$, $V_{CE} = 4.0\text{ V}$)		h_{FE}	40 20	– 100	–
Collector–Emitter Saturation Voltage ($I_C = 3.0\text{ A}$, $I_B = 0.3\text{ A}$) ($I_C = 10\text{ A}$, $I_B = 2.5\text{ A}$)		$V_{CE(sat)}$	– –	1.0 4.0	Vdc
Base–Emitter On Voltage ($I_C = 3.0\text{ A}$, $V_{CE} = 4.0\text{ V}$) ($I_C = 10\text{ A}$, $V_{CE} = 4.0\text{ V}$)		$V_{BE(on)}$	– –	1.6 3.0	Vdc
DYNAMIC CHARACTERISTICS					
Small–Signal Current Gain ($I_C = 0.5\text{ A}$, $V_{CE} = 10\text{ V}$, $f = 1.0\text{ kHz}$)		h_{fe}	20	–	–
Current–Gain — Bandwidth Product ($I_C = 0.5\text{ A}$, $V_{CE} = 10\text{ V}$, $f = 1.0\text{ MHz}$)		f_T	3.0	–	MHz

2. Pulse Test: Pulse Width $\leq 300\ \mu\text{s}$, Duty Cycle $\leq 2.0\%$.

TIP33A, TIP33C

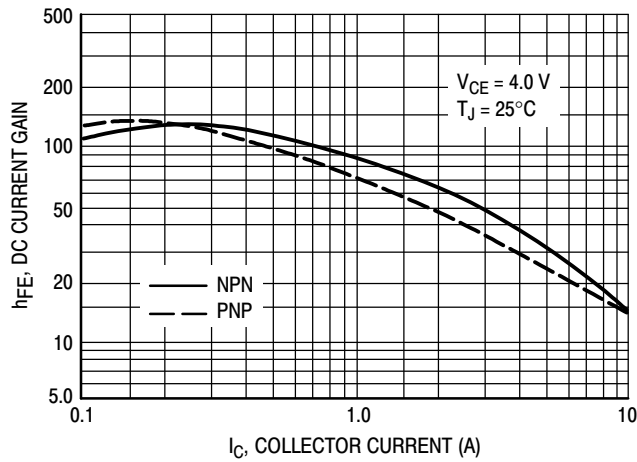


Figure 1. DC Current Gain

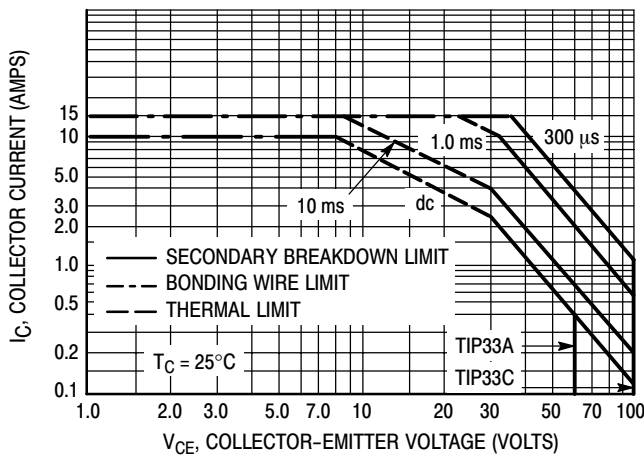


Figure 2. Maximum Rated Forward Bias Safe Operating Area

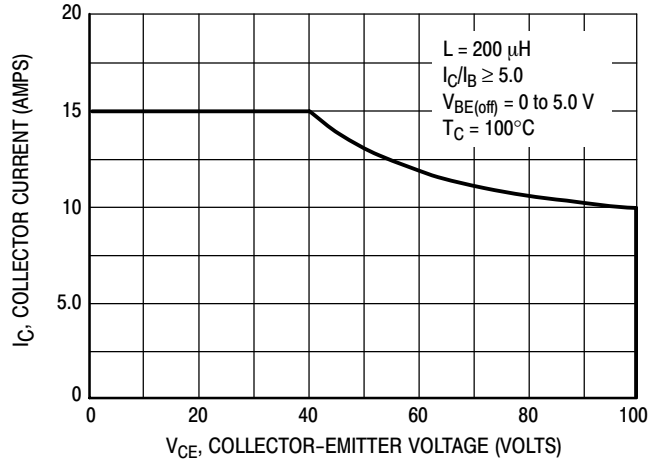


Figure 3. Maximum Rated Forward Bias Safe Operating Area

FORWARD BIAS

The Forward Bias Safe Operating Area represents the voltage and current conditions these devices can withstand during forward bias. The data is based on $T_C = 25^\circ\text{C}$; $T_{J(pk)}$ is variable depending on power level. Second breakdown pulse limits are valid for duty cycles to 10%, and must be derated thermally for $T_C > 25^\circ\text{C}$.

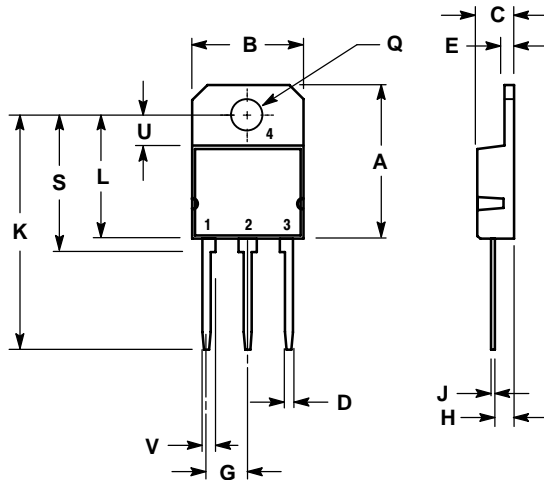
REVERSE BIAS

The Reverse Bias Safe Operating Area represents the voltage and current conditions these devices can withstand during reverse biased turn-off. This rating is verified under clamped conditions so the device is never subjected to an avalanche mode.

TIP33A, TIP33C

PACKAGE DIMENSIONS

SOT-93 (TO-218)
CASE 340D-02
ISSUE E




NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	---	20.35	---	0.801
B	14.70	15.20	0.579	0.598
C	4.70	4.90	0.185	0.193
D	1.10	1.30	0.043	0.051
E	1.17	1.37	0.046	0.054
G	5.40	5.55	0.213	0.219
H	2.00	3.00	0.079	0.118
J	0.50	0.78	0.020	0.031
K	31.00 REF		1.220 REF	
L	---	16.20	---	0.638
Q	4.00	4.10	0.158	0.161
S	17.80	18.20	0.701	0.717
U	4.00 REF		0.157 REF	
V	1.75 REF		0.069	

STYLE 1:

- PIN 1. BASE
2. COLLECTOR
3. EMITTER
4. COLLECTOR

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TIP33C/D